ChunZheng

High-end Power Semiconductor Manufacturer

ZP3200A 6200-6500V

Standard Rectifier Diode

- High power cycling capability
- Low on-state and switching losses
- Optimized for line frequency rectifiers
- Designed for traction and industrial applications

Average forward current		I_{FAV}	3200 A
Repetitive peak reverse voltage		V_{RRM}	6200 – 6500 V
V_{RRM}, V	6200	6400	6500
Voltage code	62	64	65
T_j, °C	-60 – 150		

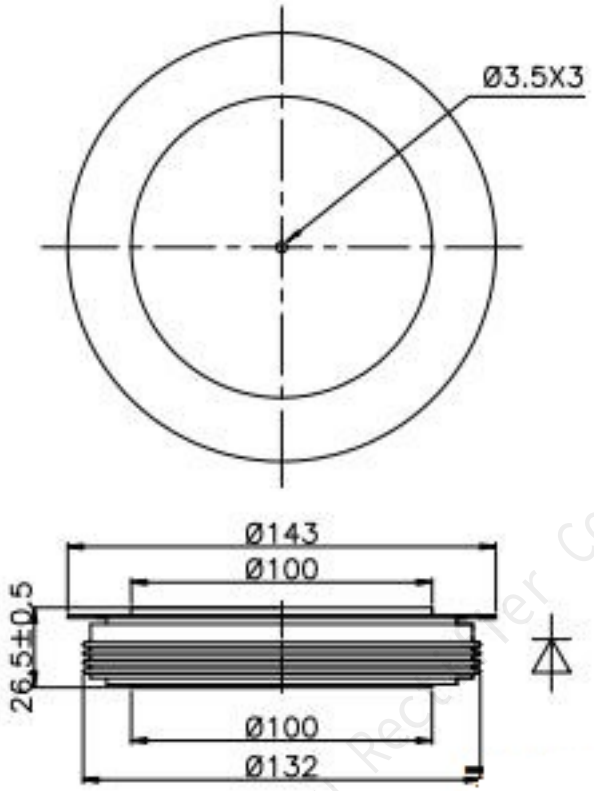
MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I_{FAV}	Average forward current	A	3200	T_c=100 °C; Double side cooled; 180° half-sine wave; 50 Hz	
I_{FRMS}	RMS forward current	A	5024	T_c=111 °C; Double side cooled; 180° half-sine wave; 50 Hz	
I_{FSM}	Surge forward current	kA	64.0 73.6	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; t_p=10 ms; single pulse; V_R=0 V;
			67.2 77.3	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; t_p=8.3 ms; single pulse; V_R=0 V;
I^2t	Safety factor	$A^2s\cdot10^3$	20480 27085	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; t_p=10 ms; single pulse; V_R=0 V;
			18741 24785	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; t_p=8.3 ms; single pulse; V_R=0 V;
BLOCKING					
V_{RRM}	Repetitive peak reverse voltages	V	6200 – 6500	$T_{j\,min}$< T_j <$T_{j\,max}$; 180° half-sine wave; 50 Hz;	
V_{RSM}	Non-repetitive peak reverse voltages	V	6300 – 6600	$T_{j\,min}$< T_j <$T_{j\,max}$; 180° half-sine wave; single pulse;	
V_R	Reverse continuous voltages	V	0.75·V_{RRM}	T_j=$T_{j\,max}$;	
THERMAL					
T_{stg}	Storage temperature	°C	-60 – 55		
T_j	Operating junction temperature	°C	-60 – 150		
MECHANICAL					
F	Mounting force	kN	70.0 – 90.0		
a	Acceleration	m/s^2	50 100	Device unclamped Device clamped	

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V_{FM}	Peak forward voltage, max	V	1.86	T_j=25 °C; I_{FM}=6300 A	
$V_{F(TO)}$	Forward threshold voltage, max	V	0.91	$T_j=T_{j\,max}$; 0.5 π I_{FAV} < I_T < 1.5 π I_{FAV}	
r_T	Forward slope resistance, max	mΩ	0.210		
BLOCKING					
I_{RRM}	Repetitive peak reverse current, max	mA	300	$T_j=T_{j\,max}$; $V_R=V_{RRM}$	
SWITCHING					
Q_{rr}	Total recovered charge, max	μC	17000	$T_j=T_{j\,max}$; I_{TM}=2000 A ; di_R/dt=-5 A/μs ; V_R=100 V;	
t_{rr}	Reverse recovery time, max	μs	140		
I_{rrM}	Peak reverse recovery current, max	A	240		
THERMAL					
R_{thjc}	Thermal resistance, junction to case, max	°C/W	0.0050	Direct current	Double side cooled
R_{thjc-A}			0.0150		Anode side cooled
R_{thjc-K}			0.0075		Cathode side cooled
R_{thck}	Thermal resistance, case to heatsink, max	°C/W	0.0010	Direct current	
MECHANICAL					
w	Weight, typ	g	2200		
D_s	Surface creepage distance	mm (inch)	49.5 (1.949)		
D_a	Air strike distance	mm (inch)	22.4 (0.882)		

OVERALL DIMENSIONS



ZT110

All dimensions in millimeters

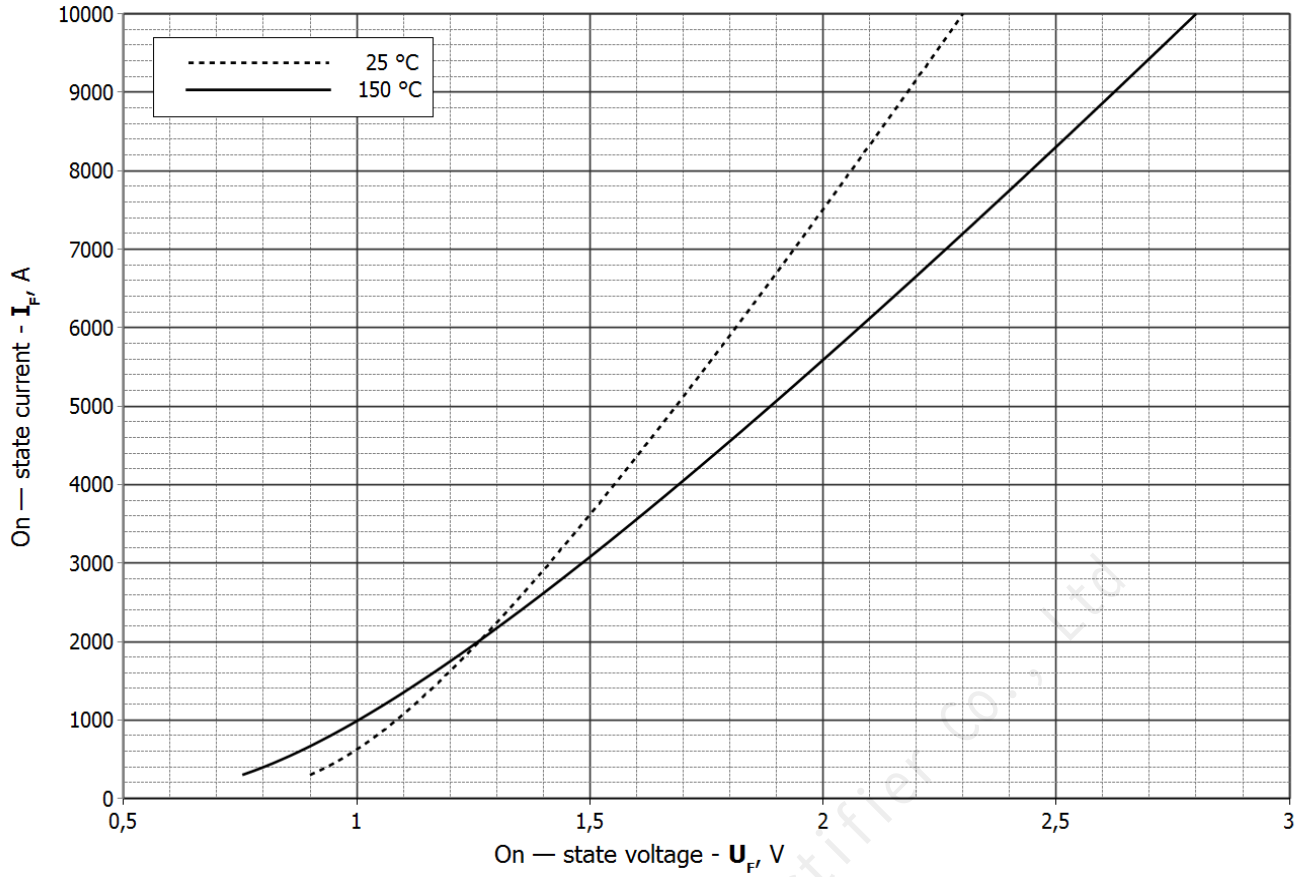


Fig 1 – Forward characteristics of Limit device

Analytical function for Forward characteristic:

$$V_F = A + B \cdot i_F + C \cdot \ln(i_F + 1) + D \cdot \sqrt{i_F}$$

	Coefficients for max curves	
	T_j = 25°C	$T_j = T_{j\,max}$
A	0,43226000	0,31016000
B	0,00010089	0,00013849
C	0,07015300	0,05148900
D	0,00212680	0,00630740

Forward characteristic model (see Fig. 1).

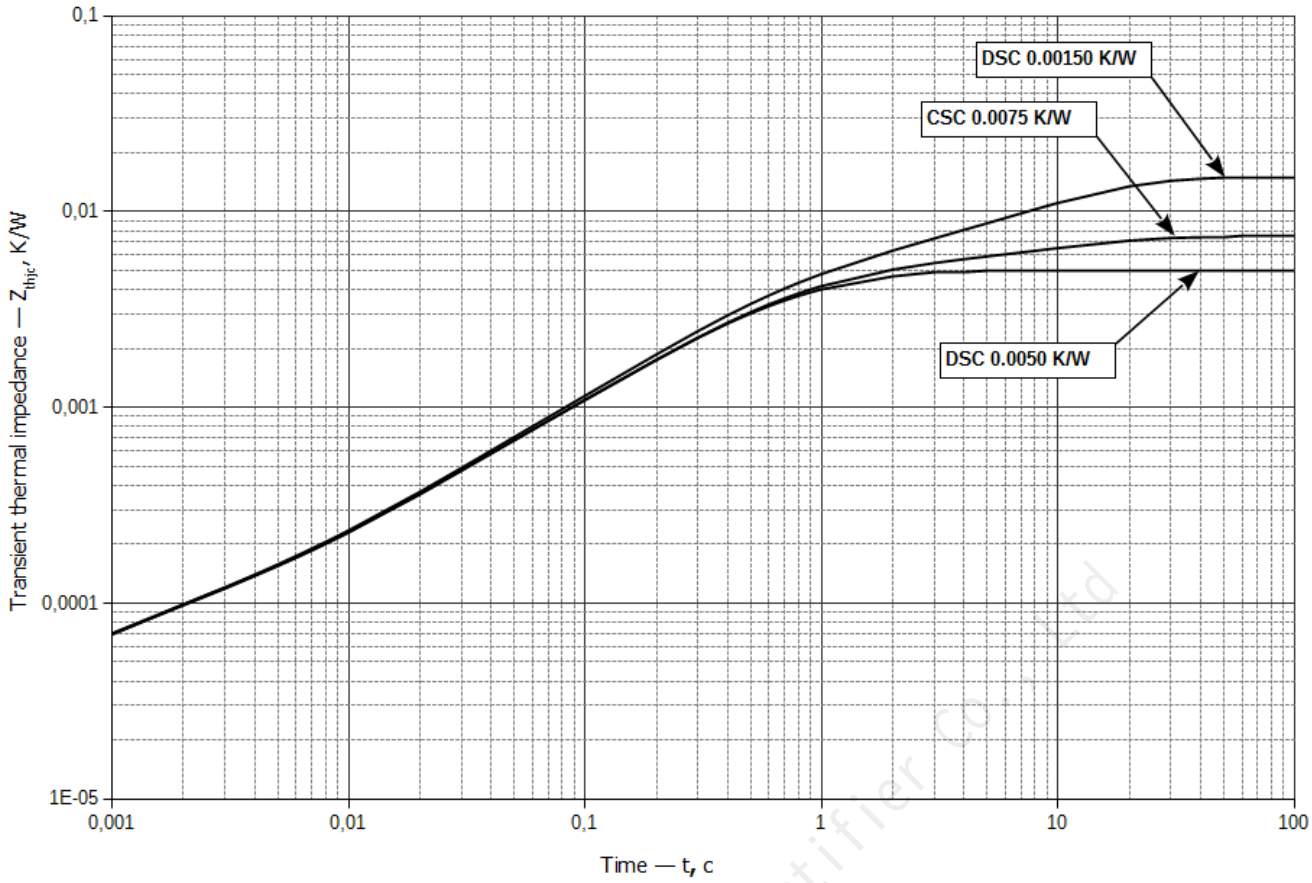


Fig 2 – Transient thermal impedance

Analytical function for Transient thermal impedance junction to case Z_{thjc} for DC:

$$Z_{thjc} = \sum_{i=1}^{n} R_i \left(1 - e^{-\frac{t}{\tau_i}}\right)$$

Where ***i*** = 1 to ***n***, ***n*** is the number of terms in the series.

t = Duration of heating pulse in seconds.

Z_{thjc} = Thermal resistance at time t.

R_i = Amplitude of p_{th} term.

τ_i = Time constatnt of r_{th} term.

DC Double side cooled

i	1	2	3	4	5	6
R_i, K/W	0.002027	0.0001166	0.002627	0.0001539	3.237e-005	4.335e-005
τ_i, s	1.059	0.080	0.3836	0.02289	0.0003559	0.001397

DC Cathode side cooled

i	1	2	3	4	5	6
R_i, K/W	0.002502	0.002188	0.002508	0.0002154	3.854e-005	4.646e-005
τ_i, s	10.6	1.090	0.3745	0.03207	0.002565	0.0004383

DC Anode side cooled

i	1	2	3	4	5	6
R_i, K/W	0.01	0.002218	0.00248	0.0002153	3.862e-005	4.604e-005
τ_i, s	10.6	1.120	0.3786	0.03196	0.002513	0.0004352

Transient thermal impedance junction to case Z_{thjc} model (see Fig. 2)

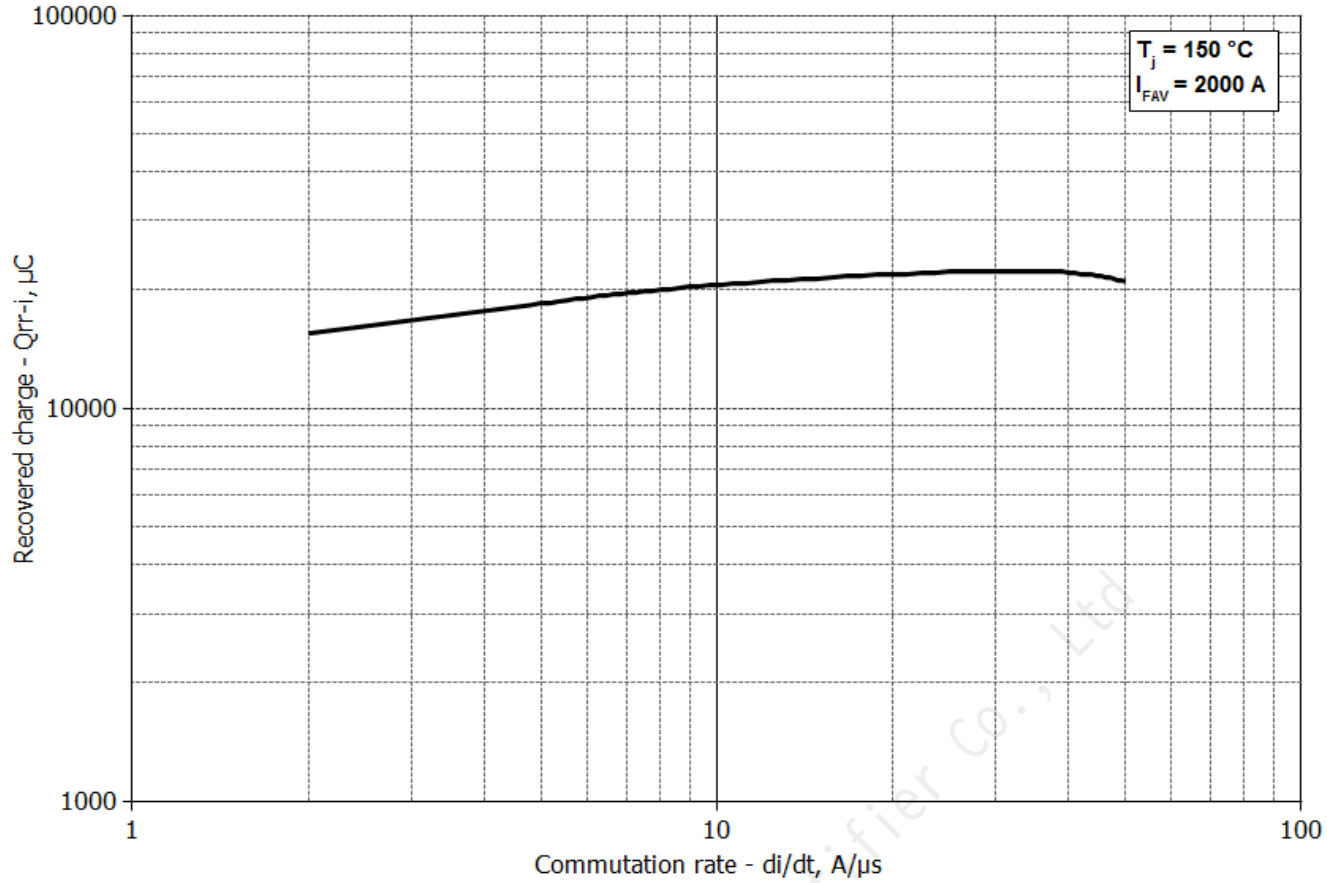


Fig 3 – Total recovered charge, Q_{rr-i} (integral)

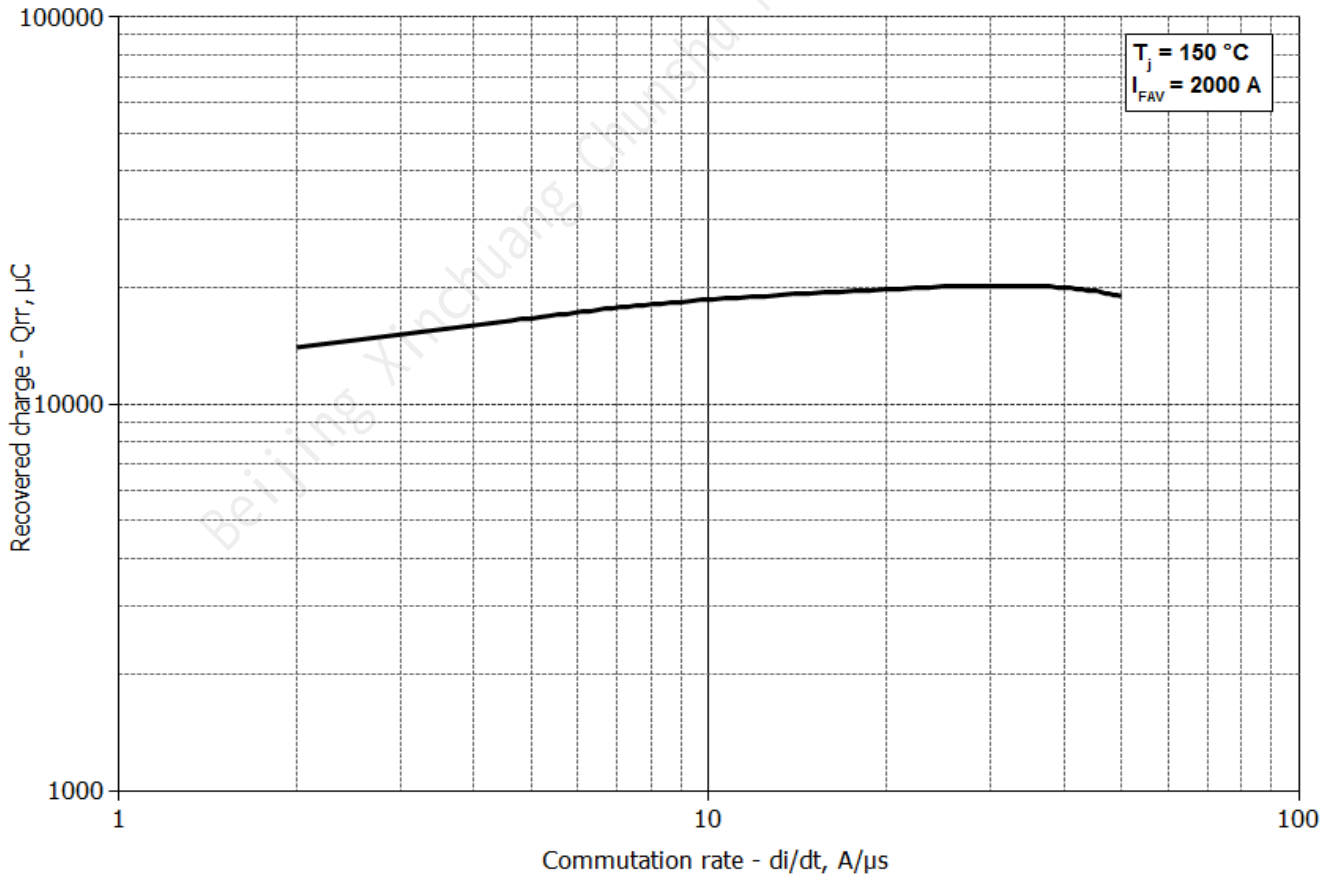


Fig 4 - Recovered charge, Q_{rr} (25% chord)

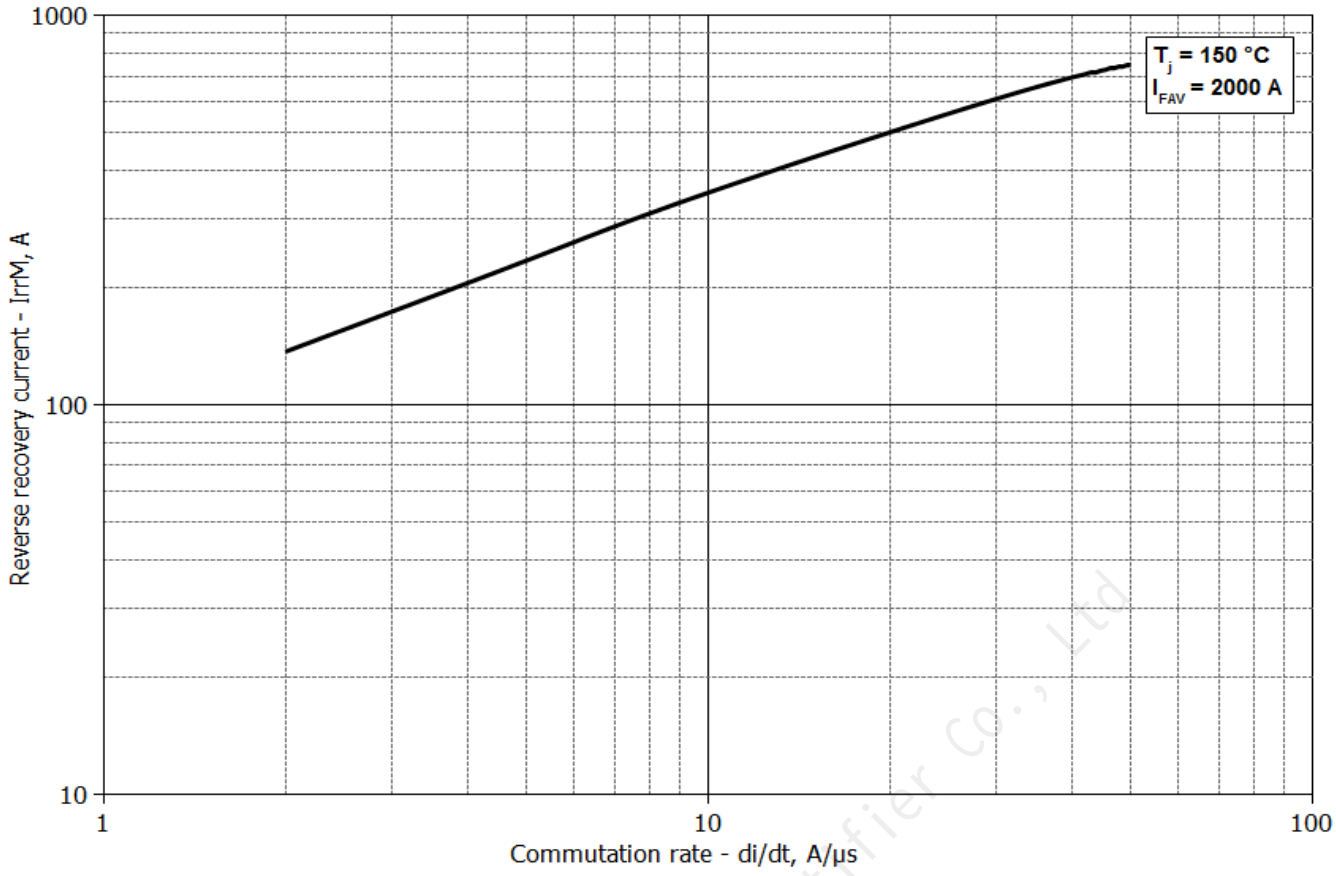


Fig 5 – Peak reverse recovery current, I_{rm}

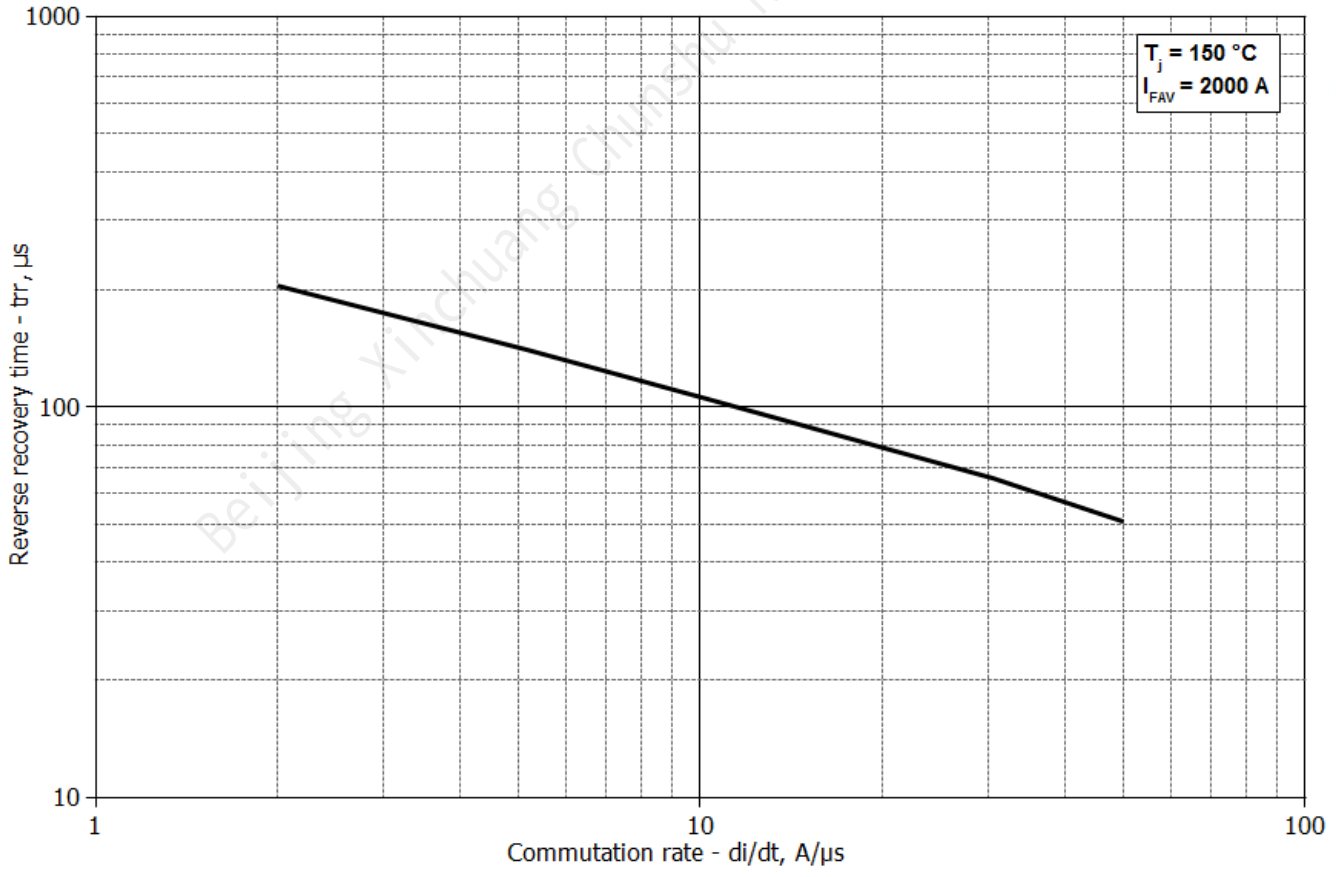


Fig 6 – Maximum recovery time, t_{rr} (25% chord)

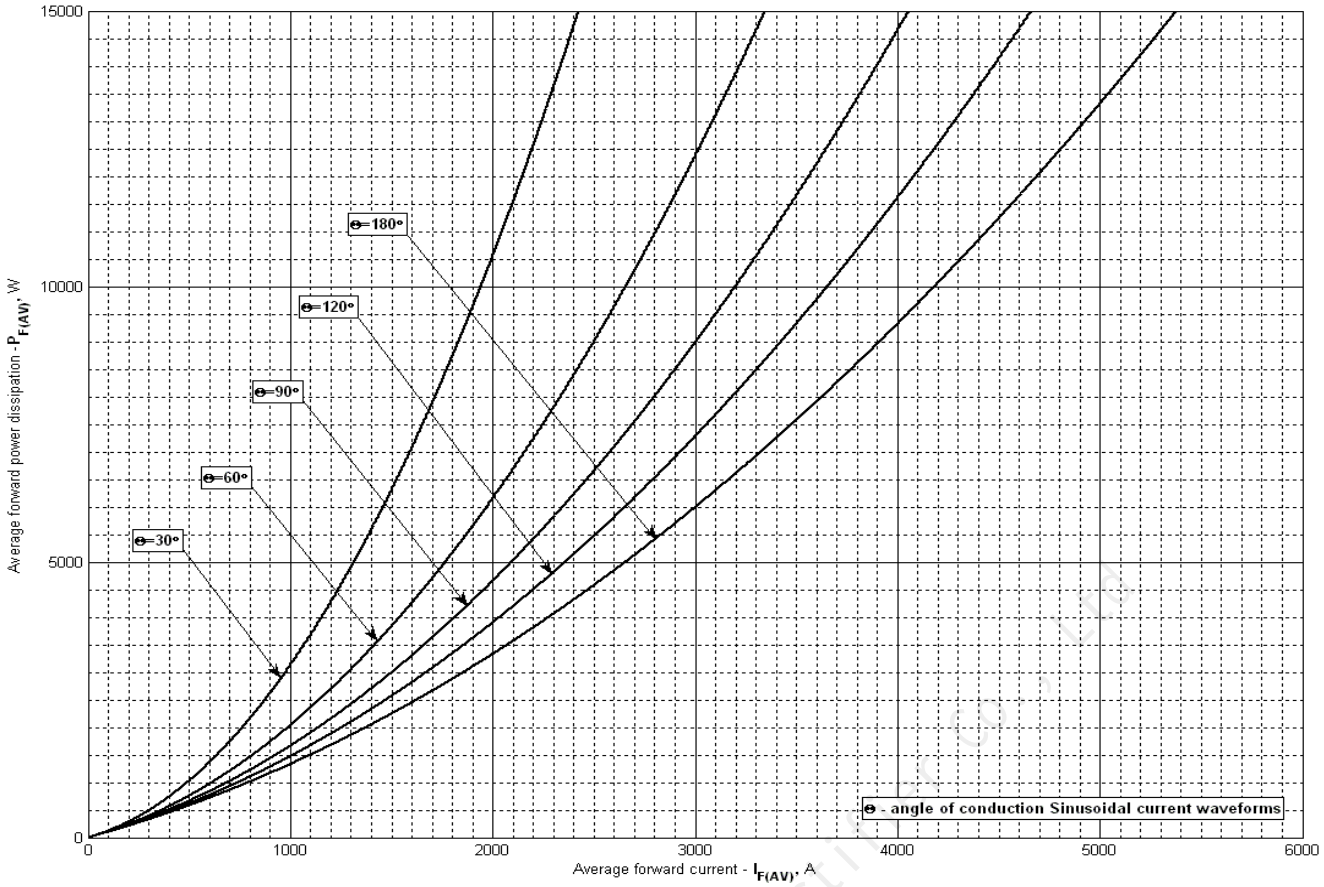


Fig 7 - Mean forward power dissipation P_{FAV} vs. Mean forward current I_{FAV} for sinusoidal current waveforms at different conduction angles (f=50Hz, DSC)

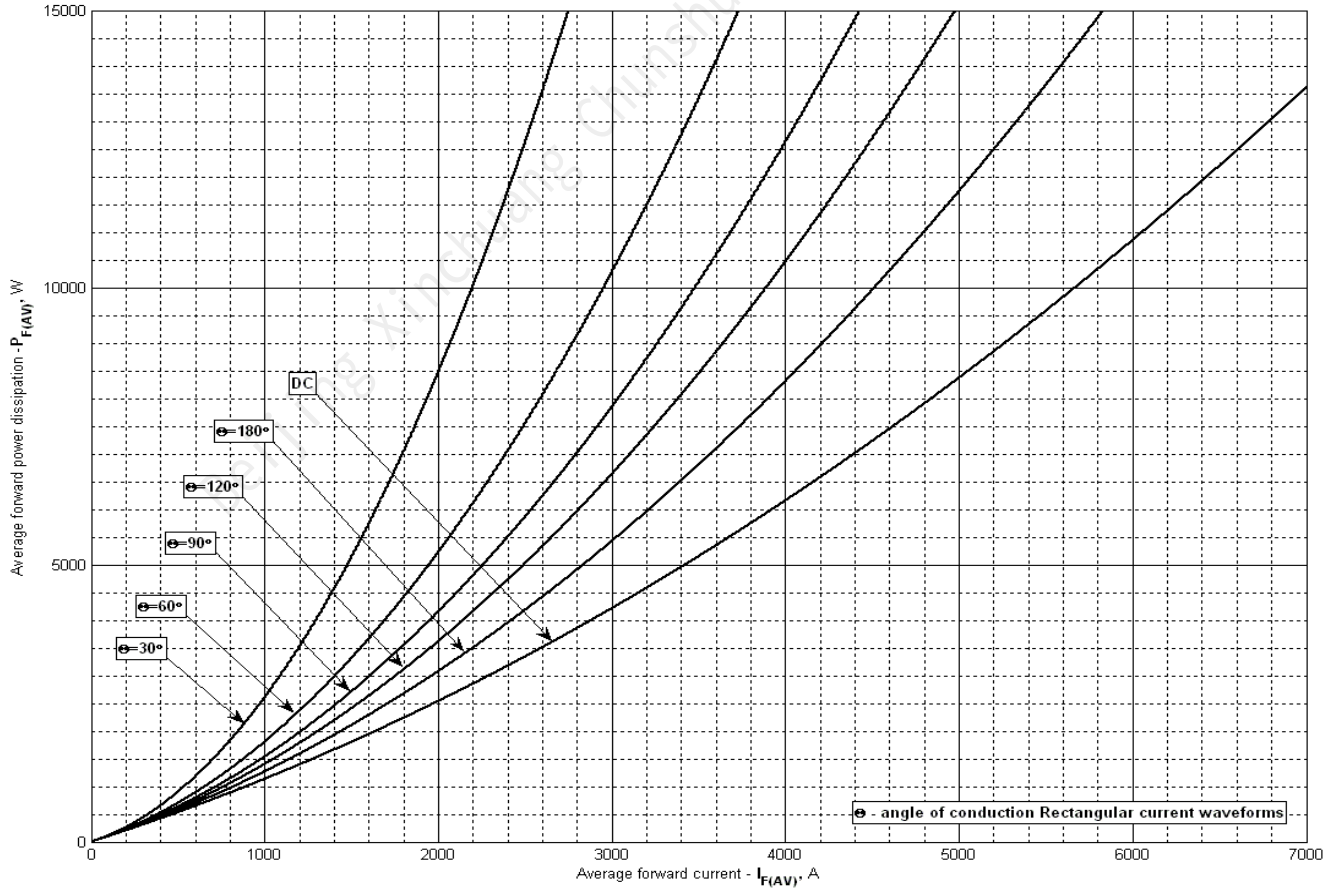


Fig 8 – Mean forward power dissipation P_{FAV} vs. Mean forward current I_{FAV} for rectangular current waveforms at different conduction angles and for DC (f=50Hz, DSC)

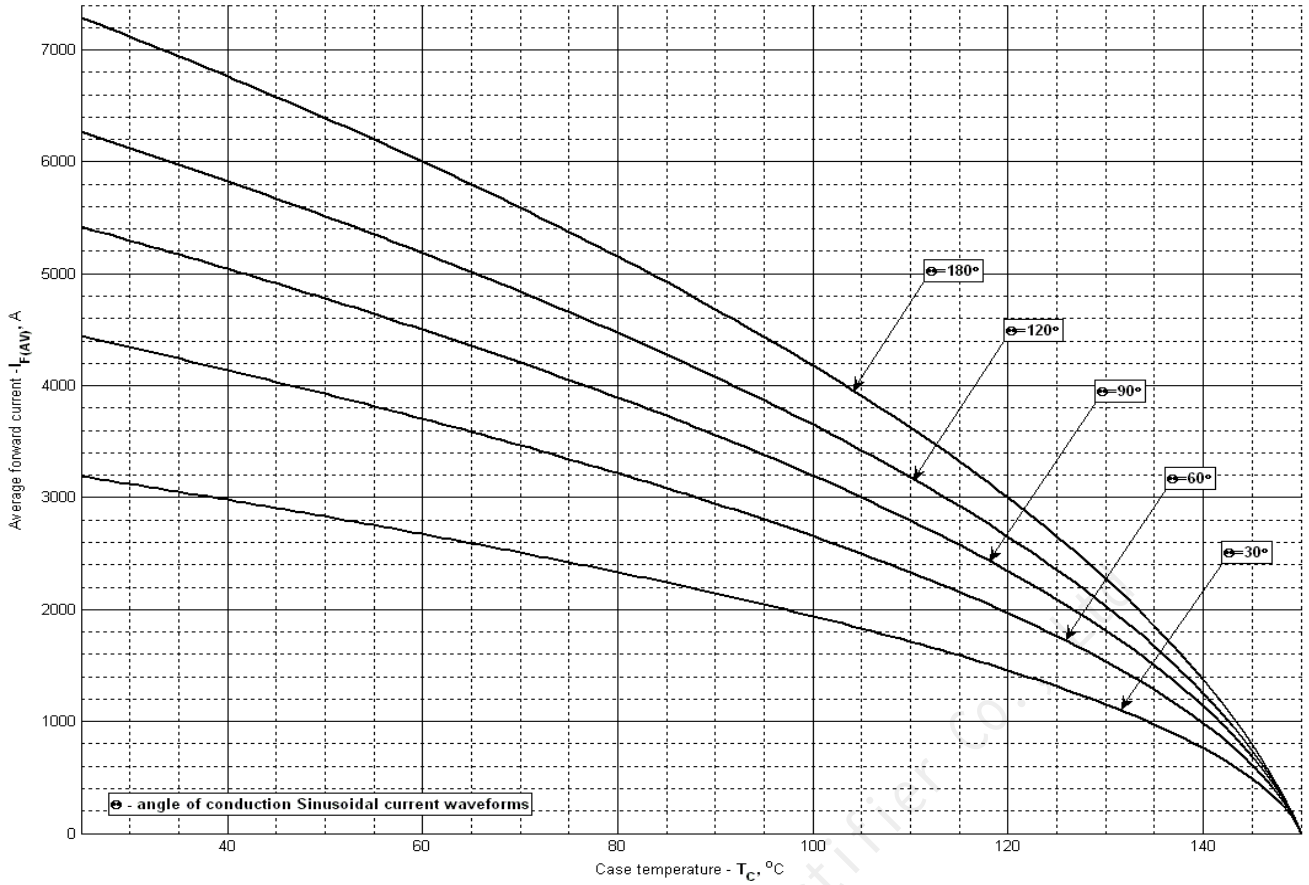


Fig 9 – Mean forward current I_{FAV} vs. Case temperature T_C for sinusoidal current waveforms at different conduction angles (f=50Hz, DSC)

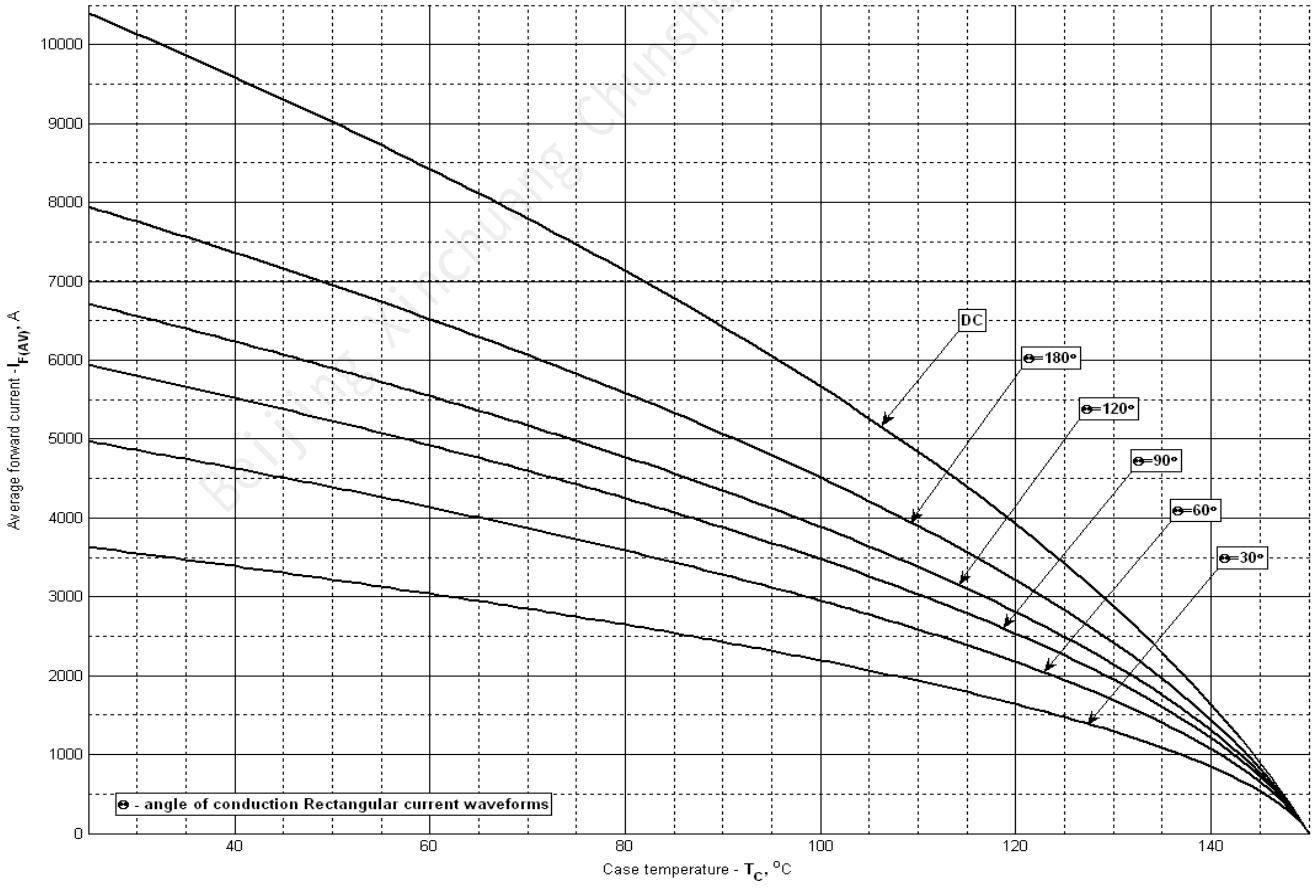


Fig 10 - Mean forward current I_{FAV} vs. Case temperature T_C for rectangular current waveforms at different conduction angles and for DC (f=50Hz, DSC)

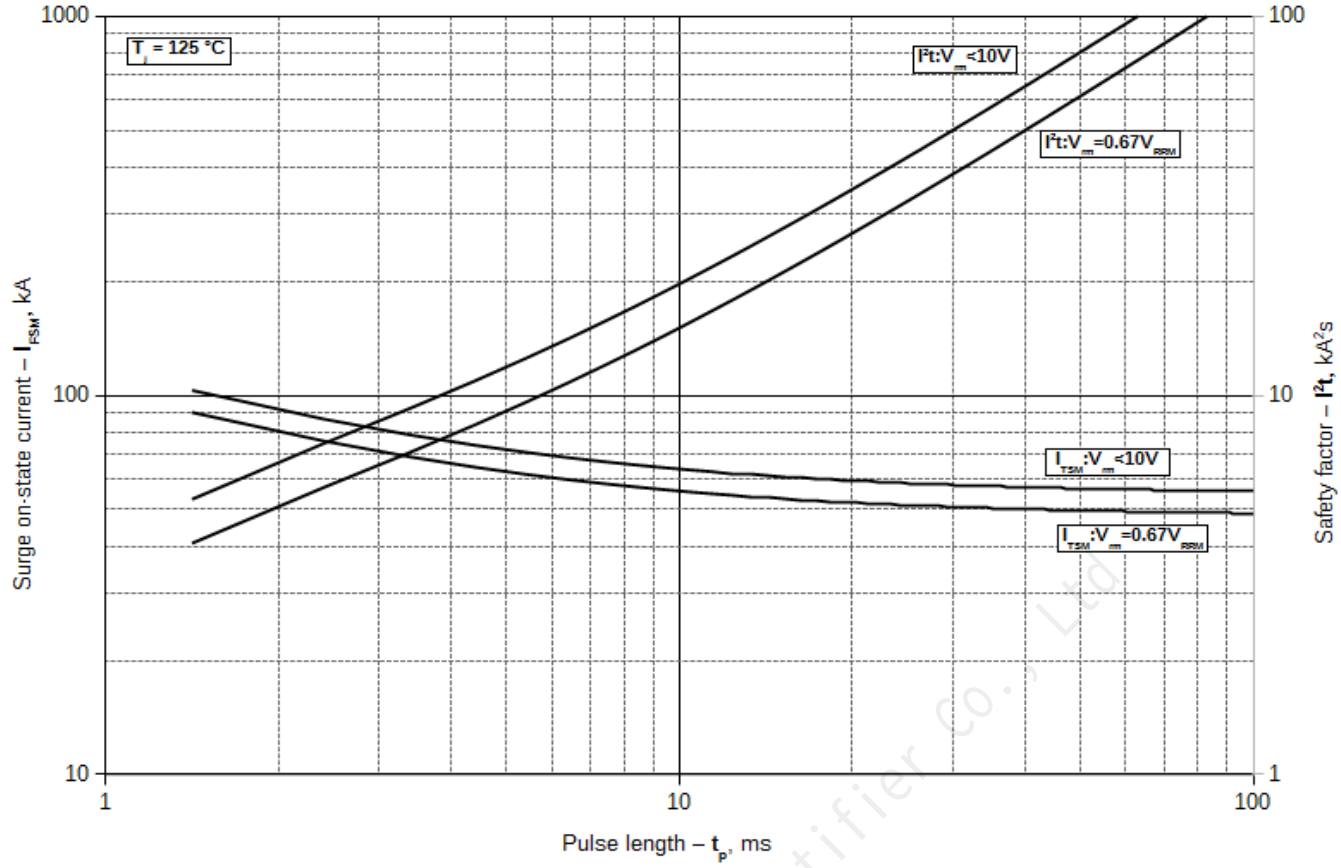


Fig 11 – Maximum surge and I^2t ratings

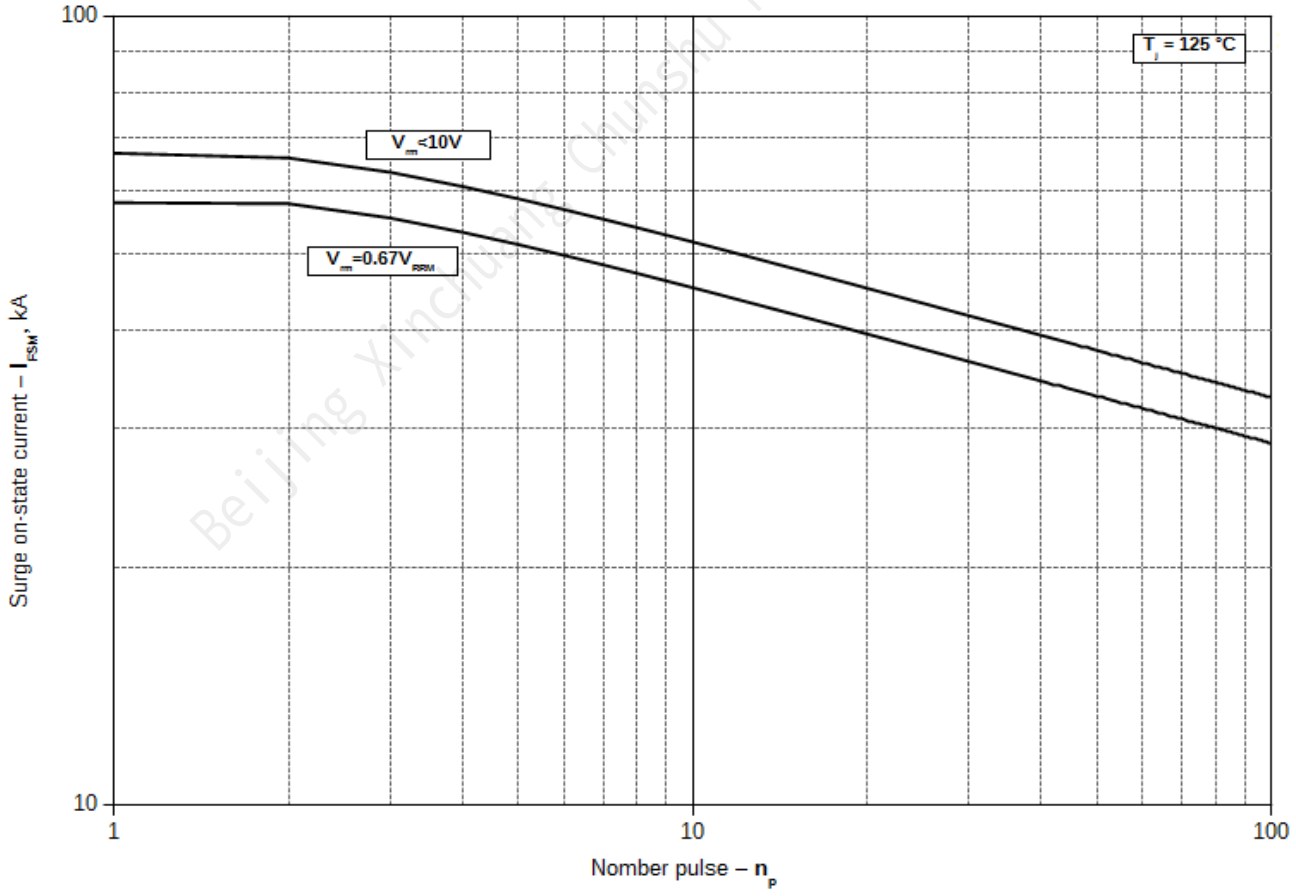


Fig 12 - Maximum surge ratings

